

IN THE CLAIMS:

1. (Currently Amended) A method of forming a source/drain of a transistor, comprising:
forming a recess in a substrate adjacent a gate of said transistor;
forming a conductive deep doped region below a bottom surface of said recess; and
epitaxially growing a semiconductor material within said recess to form said source/drain.
2. (Original) The method as recited in Claim 1 further comprising forming a lightly doped drain region adjacent said gate.
3. (Original) The method as recited in Claim 1 wherein said semiconductor material is silicon.
4. (Currently Amended) The method as recited in Claim 1 wherein said forming said conductive deep doped region is performed by an ion implantation process.
5. (Original) The method as recited in Claim 4 wherein said ion implantation process comprises implanting one of P-type ions and N-type ions.

Claims 6.- 10. (Cancelled)

11. (Currently Amended) A method of forming a transistor, comprising:
providing a gate on a substrate, including:
 forming a gate dielectric over said substrate, and
 forming a gate electrode over said gate dielectric; and
providing a source/drain, including:
 forming a recess in said substrate adjacent said gate,
 forming a conductive deep doped region below a bottom surface of said recess;
and
 epitaxially growing a semiconductor material within said recess to form said
source/drain.
12. (Original) The method as recited in Claim 11 wherein said providing said
source/drain further includes forming a lightly doped drain region adjacent said gate.
13. (Original) The method as recited in Claim 11 wherein said semiconductor material is
silicon.
14. (Currently Amended) The method as recited in Claim 11 wherein said forming said
conductive deep doped region is performed by an ion implantation process.
15. (Original) The method as recited in Claim 14 wherein said ion implantation process
comprises implanting one of P-type ions and N-type ions.

16. (Original) The transistor as recited in Claim 11 further comprising providing another source/drain, including:

forming another recess in said substrate adjacent said gate;

forming a deep doped region below a bottom surface of said another recess; and

epitaxially growing a semiconductor material within said another recess to form said another source/drain.

17. (Original) The method as recited in Claim 16 wherein said providing said another source/drain further includes forming a lightly doped drain region adjacent said gate.

18. (Original) The method as recited in Claim 16 wherein said semiconductor material is silicon.

19. (Original) The method as recited in Claim 11 wherein said providing said gate further includes forming spacers on opposing walls of said gate dielectric and gate electrodes.

20. (Original) The method as recited in Claim 11 wherein said providing said gate and said source/drain further include performing a salicide process to form contacts thereon.